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APPLICATION NO. FILING DATE		FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.		
09/957,000 09/19/2001		Anisul Khan	005606/ETCH/SILICON/JB1 2442			
32588 7	590 09/22/2003		12			
APPLIED MATERIALS, INC.			EXAMI	EXAMINER		
2881 SCOTT BLVD. M/S 2061 SANTA CLARA, CA 95050			AHMED, SHAMIM			
			ART UNIT	PAPER NUMBER		
			1765			
		DATE MAILED: 09/22/2003				

Please find below and/or attached an Office communication concerning this application or proceeding.

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		Applicatio	n No.	Applicant(s)	(1)		
Office Action Summary		09/957,000)	KHAN ET AL.			
		Examiner		Art Unit			
		Shamim A		1765			
Period fo	The MAILING DATE of this c mmunication app	pears on the	cover sheet with the c	orrespondence address			
A SHO THE N - Exten after: - If the - If NO - Failur - Any re	DRTENED STATUTORY PERIOD FOR REPLY MAILING DATE OF THIS COMMUNICATION. Isions of time may be available under the provisions of 37 CFR 1.11 SIX (6) MONTHS from the mailing date of this communication. period for reply specified above is less than thirty (30) days, a reply period for reply is specified above, the maximum statutory period to reply within the set or extended period for reply will, by statute eply received by the Office later than three months after the mailing d patent term adjustment. See 37 CFR 1.704(b).	36(a). In no ever y within the statu will apply and will e, cause the appli	ort, however, may a reply be time ory minimum of thirty (30) day expire SIX (6) MONTHS from the cation to become ABANDONE	nely filed s will be considered timely. the mailing date of this communication D (35 U.S.C. § 133).			
1)🖂	Responsive to communication(s) filed on 15 J	July 2003 .					
2a)⊠	This action is FINAL . 2b) ☐ Th	nis action is i	non-final.				
3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213. Disposition of Claims							
4)🖂	Claim(s) 1-4 and 11-23 is/are pending in the a	application.					
	4a) Of the above claim(s) <u>17-23</u> is/are withdrav	vn from con	sideration.				
5)□	Claim(s) is/are allowed.						
6)⊠	6)⊠ Claim(s) <u>1-4 and 11-17</u> is/are rejected.						
7)	7) Claim(s) is/are objected to.						
,—	Claim(s) are subject to restriction and/o on Papers	or election re	quirement.				
9)[The specification is objected to by the Examine	er.		•			
10) 🔲 -	Γhe drawing(s) filed on is/are: a)□ acce	pted or b)	objected to by the Exa	miner.			
	Applicant may not request that any objection to the						
11) 🗌 -	The proposed drawing correction filed on			oved by the Examiner.			
If approved, corrected drawings are required in reply to this Office action.							
12) The oath or declaration is objected to by the Examiner.							
_	inder 35 U.S.C. §§ 119 and 120) () () ()			
	Acknowledgment is made of a claim for foreign	n priority un	der 35 U.S.C. § 119(a	ı)-(d) or (t).			
a)[☐ All b)☐ Some * c)☐ None of:						
1. Certified copies of the priority documents have been received.							
2. Certified copies of the priority documents have been received in Application No							
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 							
14) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).							
 a) ☐ The translation of the foreign language provisional application has been received. 15)☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121. 							
Attachment(s)							
2) Notic	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948) nation Disclosure Statement(s) (PTO-1449) Paper No(s) 9	<u>)</u> .	4) Interview Summar 5) Notice of Informal 6) Other:	y (PTO-413) Paper No(s) Patent Application (PTO-152)			

DETAILED ACTION

Election/Restrictions

1. Applicant's election with traverse of Group I, claims 1-17 in Paper No. 11 is acknowledged. The traversal is on the ground(s) that a search and examination of the entire application cannot be a serious burden. This is not found persuasive because the inventions are in fact patentable distinct each from the other, which is shown by their different classification.

The requirement is still deemed proper and is therefore made FINAL.

Response to Arguments

2. Applicant's arguments with respect to claims 1-4,11-17 have been considered but are most in view of the new ground(s) of rejection.

Claim Rejections - 35 USC § 102

3. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 4. Claims 1,3-4,11-15 and 24 are rejected under 35 U.S.C. 102(b) as being anticipated by Kawasaki et al (4,795,529).

As to claims 1, 3 and 5, Kawasaki et al disclose a process of making a deep trench within a silicon substrate, wherein etching is performed by using a series of

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repeated etching and deposition steps through a patterned masking layer having aperture (col.5, lines 45-54, col.6, lines 11-36).

Kawasaki et al also teach that the repeated etching and deposition steps forming the trench with an undulating profile, and inherently teach that the undulating profile of the trench side wall has an increased surface area (see figure 6).

As to claim 4, Kawasaki et al teach that the trench is formed on a silicon wafer having wiring layers (see figure 6).

So, the etched structure is an elevated structure.

As to claims 11-12, Kawasaki et al teach that the etching gas comprises SF_6 (col.4, lines 61-62).

As to claims 13-15 and 24, Kawasaki et al teach that the deposition gas could comprises fluorocarbon such as $C_2Cl_3F_3$ or C_4F_8 along with SF_6 as an etching gas (claim 10).

Claim Rejections - 35 USC § 103

- 5. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 6. This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein

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were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

7. Claims 2 and 16-17 rejected under 35 U.S.C. 103(a) as being unpatentable over Kawasaki et al (4,795,529) in view of McReynolds (6,191,043).

As to claim 2, Kawasaki et al discussed above in the paragraph 4 and also disclose that the etched feature has deep opening with high dimensional accuracy (col.10, lines 3-12).

Kawasaki et al fail to disclose that the trench structure has a vertical dimension in arrange of 1-10 microns.

However, it would have been obvious to have the trench opening with 1-10 microns as considered to be a deep opening with high aspect ratio in order to form an improved semiconductor integrated circuits which is supported by McReynolds.

McReynolds teaches that in order to form improved semiconductor integrated circuits, a deep opening of 3-10 microns has to form on the semiconductor substrate (col.1, lines 5-18).

Therefore, it would it would have been obvious to one skilled in the art at the time of claimed invention to combine McReynold's teaching into Kawasaki et al's process for forming an opening having high aspect ratio in order to form an improved device.

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As to claim 16, it would have been obvious to one skilled in the art to optimize the plasma density because the plasma density appears to reflect a result-effective variable, which can be optimized. See MPEP 2144.05 IIB and further more, Michaelis et al teach that the etched profile can achieved by varying ratio of the gases that will eventually varying the plasma density (col.4, lines 24-30).

As to claim 17, McReynolds teaches that the etch rate is approximately 3.5 microns per minute and an average etch rate is approximately 1.6 microns per minute (col.5, lines 24-25 and lines 44-45).

Conclusion

8. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Shamim Ahmed whose telephone number is (703) 305-1929. The examiner can normally be reached on M-Thu (7:00-5:30) Every Friday Off.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine G Norton can be reached on (703) 305-2667. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0661.

Shamim Ahmed Examiner Art Unit 1765

SA September 10, 2003

> NADINE G. NORTON PRIMARY EXAMINER